Rectifier diodes schottky barrier

BYV143F series

GENERAL DESCRIPTION

Dual, low leakage, platinum barrier, schottky rectifier diodes in a full pack plastic envelope, featuring low forward voltage drop, absence of stored charge. and guaranteed reverse surge capability. The devices are intended for use in switched mode power supplies and high frequency circuits in general where low conduction and zero switching losses are important.

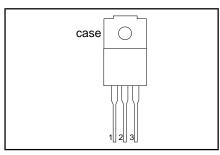
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
V_{RRM}	BYV143F- Repetitive peak reverse voltage	35 35	40 40	45 45	V
V _F I _{O(AV)}	Forward voltage Average output current (both diodes conducting)	0.62 20	0.62 20	0.62 20	V A

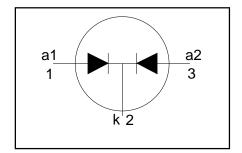
PINNING - SOT186

PIN	DESCRIPTION
1	anode 1 (a)
2	cathode (k)
3	anode 2 (a)

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
V _{RRM} V _{RWM} V _R	Repetitive peak reverse voltage Crest working reverse voltage Continuous reverse voltage	T _{hs} ≤ 112 °C		- 35 35 35 35	-40 40 40 40	-45 45 45 45	<<<
I _{O(AV)}	Average output current (both diodes conducting)	square wave; $\delta = 0.5$; $T_{hs} \le 87$ °C	-		20		Α
I _{O(RMS)}	RMS output current (both diodes conducting)	TIS = 0.	-		20		А
I _{FRM}	Repetitive peak forward current per diode	$t = 25 \mu s$; δ = 0.5; $T_{hs} \le 87 ^{\circ} C$	-		30		A
I _{FSM}	Non-repetitive peak forward current, per diode	t = 10 ms t = 8.3 ms sinusoidal T_i = 125 °C prior to surge; with reapplied $V_{RRM(max)}$	- -		100 110		A A
l ² t	I ² t for fusing	t = 10 ms	-		50		A ² s
I _{RRM}	Repetitive peak reverse current per diode.	$t_p = 2 \mu s; \delta = 0.001$	-		1		A
I _{RSM}	Non-repetitive peak reverse current per diode.	$t_{p} = 100 \ \mu s$	-		1		A
$T_{stg} \ T_{j}$	Storage temperature Operating junction temperature		-65 -		175 150		°C

Philips Semiconductors Product specification

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ISOLATION LIMITING VALUE & CHARACTERISTIC

 T_{hs} = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. ≤ 65% ; clean and dustfree	1		1500	V
C _{isol}	Capacitance from T2 to external heatsink	f = 1 MHz	-	12	1	pF

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th i-hs}		per diode	-	-	5.7	K/W
'	heatsink	both diodes	-	-	4.8	K/W
R _{th j-a}	Thermal resistance junction to ambient	(with heatsink compound) in free air.	-	55	-	K/W

STATIC CHARACTERISTICS

 $T_i = 25$ °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage (per diode)	I _F = 15 A; T _i = 150°C	-	0.55	0.62	V
		$I_{\rm F} = 20 \text{A}$	-	0.76	0.80	V
I _R	Reverse current (per diode)	$V_R = V_{RRM}$	-	10	200	μĄ
	lumation consistence (con	$V_R = V_{RRM}^{NNW}$; $T_j = 125 ^{\circ}C$ $f = 1MHz$; $V_R = 5V$; $T_i = 25 ^{\circ}C$ to	-	10	30	mA
C _d	Junction capacitance (per diode)	$ T = 1 \text{MHZ}; V_R = 5 \text{V}; I_j = 25 \text{ C to} 125 ^{\circ}\text{C}$	-	500	1	pF

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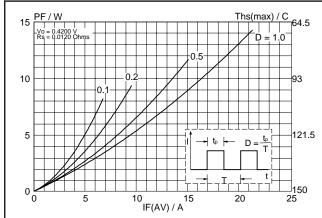


Fig.1. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; square current waveform where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

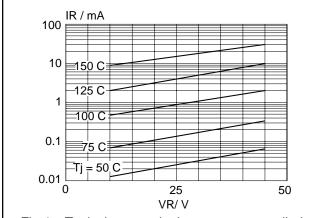


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

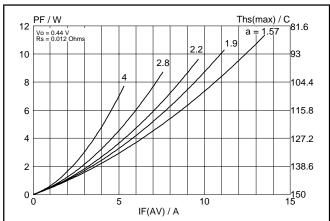


Fig.2. Maximum forward dissipation $P_F = f(I_{F(AV)})$ per diode; sinusoidal current waveform where a = f form factor $= I_{F(RMS)} / I_{F(AV)}$.

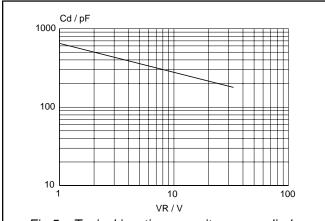


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

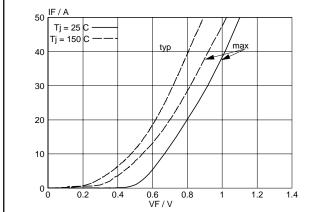


Fig.3. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_i

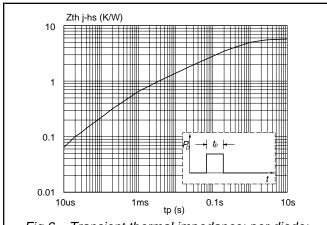
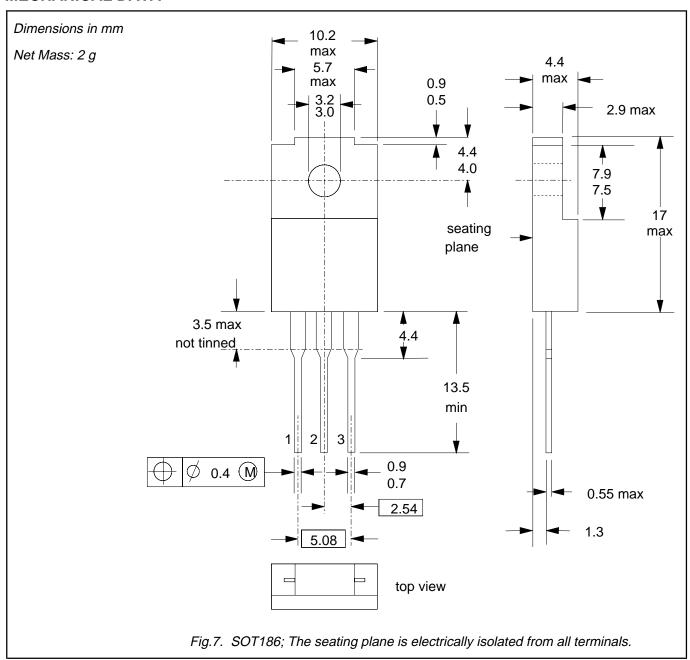


Fig.6. Transient thermal impedance; per diode; $Z_{th j - hs} = f(t_p)$.

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MECHANICAL DATA



- Notes
 1. Refer to mounting instructions for F-pack envelopes.
 2. Epoxy meets UL94 V0 at 1/8".

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DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

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